

EAST - [t0785310 trench NROM w/ p-1]

File Edit View Insert Options Tools Help

Active

- > L1: (159301) (nrom read adj only adj memory)
- > L2: (1110/785310)
- > L3: (221216) (sonos monos mnos nrom nitride adj3 memory)
- > L4: (771) (nrom)
- > L5: (1990) (nonvolatile non adj volatile adj read adj only)
- > L6: (714 with 5)
- > L7: (1932) (nrom nitride adj read adj only adj memory)
- > L8: (1991) (nitride adj read adj only adj memory)
- > L9: (392) (nitride adj read adj only)
- > L10: (322) 8 with 4
- > L11: (88825) trench\$9
- > L12: (822) 8 4
- > L13: (32) 11 with 12
- > L14: (46) 11 same 12
- > L15: (7852821) (select\$4 side control adj (gate line) \$6
- > L16: (77) 14 and 15
- > L17: (168) 11 and 12
- > L18: (6844901) (select\$4 side 1 adj (gate line) \$6
- > L19: (68) 17 and 18
- > L20: (1251634) group\$3
- > L21: (2112 with 20)
- > L22: (2) 12 same 20
- > L23: (559) nor adj memory
- > L24: (4) 23 with 11
- > L25: (151) 23 same 11

29 same 11

April 2005

#	I	Inventor	Document Issue P.	Title	Current Current I Retirev S C P	Image	Def
1	<input type="checkbox"/>	Ding, Yi	US 200500 2005 3	Fabrication of conductive gates for non	438/25 438/268	P	US 20050
2	<input type="checkbox"/>	Ding, Yi	US 200402 200413	Fabrication of dielectric on a gate surf	438/58 438/197	P	US 20040
3	<input type="checkbox"/>	Ding, Yi	US 200402 200413	FABRICATION OF GATE DIELECTRIC IN NOR	438/25	P	US 20040
4	<input type="checkbox"/>	Ding, Yi	US 200402 200413	FABRICATION OF GATE DIELECTRIC IN NOR	438/25/31	P	US 20040
5	<input type="checkbox"/>	Ding, Yi	US 200402 2004151	NOR VOLATILE MEMORIES WITH A FLOATING	257/31 297/316	P	US 20040
6	<input type="checkbox"/>	Ding, Yi	US 2004018 2004 47	Nonvolatile memories and methods of	438/25 438/268	P	US 200401
7	<input type="checkbox"/>	Ding, Yi	US 2004018 2004 5	Nonvolatile memories and methods of	438/25 257/316	P	US 200401
8	<input type="checkbox"/>	Ding, Yi	US 2004018 2004 4	Fabrication of integrated circuit elem	438/25	P	US 200401
9	<input type="checkbox"/>	Forbes, Lee	US 200502 2005 2	Nor flash memory cell with high storag	365/18	P	US 20050
10	<input type="checkbox"/>	Li Chi Han &	US 200201 2002 11	Non-volatile memory with a serial tran	257/29 257/E27.10	P	US 200201